APPLICATION FOR ESCC QUALIFICATION APPROVAL									age 1	1	
E	SCC	ircuits -M7 M	s, Silicon, Mon icrocontroller	olithic,	, Radiation-Hardened 3	2-bit	Ap	opl. N	0.		
The second second		Executive Member:	CNES				Date: 12/03/202	21	3	72	
Components (including	g series and families) s	ubmitted for Qualificati	on Approval								1
ESCC COMPONENT. NO.	VARIANTS	RANGE OF CO	MPONENTS	S	BASED ON)	TEST VEHICLE / S		COMPC SIMIL	NEN _AR	Т
9512/006	01	Integrated Circuits, Monolithic, Radiatic bit ARM Cortex-M7	Silicon n-Hardened Microcontro	l 32- oller	SAMRH71 - ATMX150RH technology	HA	SAMRH71 CQFP- 256				
Component Manufacturer 2 Location of Manufacturing Plant 3 ESCC Specification used for Qualification MICROCHIP TECHNOLOGY NANTES MCHP Nantes (design & test) UMC Taïwan (wafer fab 8C) MMT Thailand (assembly) Generic: ESCC 9000 issue 10 Issue Detail/s: ESCC 9000 issue 10									1	4	
Qualification Report R	eference and date:	-	5	PID	used for manuf	acturing	g Qualification Lot				6
SoC ARM Developme Rev2	nt SAMV71RHBD - PU	IMA - ESCC Evaluation	Report	Ref I	No: SAI	MRH71	PID 0040 rev. 0				
Date: 09/02/20	21			Issue	lssue: Rev 0						
				Date	: 12/	03/2021	1				
None	art of qualification	/	Current P	עוי עוי	erified by C	NES Name	of Executive Represent	ative A	aencv		8
Minor*			Ref No:			SAM	RH71 PID 0040 rev. 0 – 1	12/03/2	021		
Major*						MMT 04/02	PID FOR MCHP NANTE /2019	S – 1G	-QM-010)5 –	
Current Manufacturing	facilities surveyed by:										9
CNES (D. Dangla, F.	Malou) & ESA (F. Mart	inez)	10/07/20	19			_				
(Name of Executive R	esponsible)		(Date)								
Report Reference - E	SCC Audit of MMT As	sembly for ATC18RHA	and ATMX1	150RH	IA ASICs - DSC	D/AQ/E0	C-2019.0013984, 30/08/2	2019			
Satisfactory:	Yes 🖂	No 🗆 Ex	kplain								
Quality and Reliability	Data										10
Evaluation testing per	formed Yes 🖂	No 🗆		F	ailure analysis available	, DPA, I	NCCS Yes	\boxtimes	No		
Report Ref. No.: E	SCC Evaluation Repor 020-EC-731 Rev2	t Date: 01/1	2/2020	(:	supply data)						
Equivalent Data: Si	ingle Phase Qualificatio	on applies									
Certification:				F	Ref Nos. and pu	urpose:					
				C	Construction an	alysis r	eport MCHP/SERMA Re	port 20	-1705-10	0 06/	2020

	AF	PLICATION FOR ESCC QUALI	FICATION APPROVAL	Page 2
ESCC	Component Title:	Integrated Circuits, Silicon, M based on Type ATMX150RHA 5ML+Thick Metal MMT	lonolithic, CMOS, Cell-Based Array, A – Ph2 Digital Only 22Mgates	Appl. No.
	Executive Member:	CNES	Date: 12/03/2021	372
The undersigned hereby certifies on behal that the appropriate documentation has be except as stated in box 13; that the reports given to the component(s) listed herein.	f of the ESCC Executiven evaluated; that full and data are availabl	ve, that the above information is o compliance to all ESCC requiren e at the ESCC Executive and the	correct; ients is evidence refore applies for ESCC qualification status	s to be
Data 40/00/0004				Wneuc
Date: 12/03/2021			JP. BUSSENOT	coordinator)
Continuation of Boxes above: (Only non-co	onfidential comments)			12
[5] SoC ARM Development SAMV71RHBE	0 - PUMA - ESCC Eva	luation Report - CNES contract 1	80954 DL6.8.3 rev2 and associated reports	5:
 ATMX150RHA Qualification Test Report ATMX150RHA Process Identification Doo MMT - Assembly of multi-decks & Flat-su SAMRH71 ESCC Evaluation Plan - CNE SAMRH71 Process Identification Docume SAMRH71 ESCC Detail Specification - C SAMRH71 Electrical characterization rep Rapport de test ions lourds - CNES contr Rapport de test en dose cumulée - CNES SAMRH71F20C Radiation Test Report - 	- QTR 2018-IC-384 re cument - PID0037 revit lisbrate packages - Qu S contract 180954 DL0 ent - CNES contract 180954 ort - CNES contract 180954 ort - CNES contract 18 act 180954 DL5.7.2 re S contract 180954 DL5 rev 5.0 - December 20	v1 Definition Test Report - QTR 201 5.8.1 rev1.0 30954 DL6.8.5 - PID0040 rev0 DL6.8.4 draft C 30954 DL4.6.4 rev1.1 v1 .7.4 rev1 20	7-EC-212 rev2	
 Construction Analysis on a SAMRH71F2 	0C-7GB-SV Microcont	roller from Microchip, Report 20-	705-100 - June 10th, 2020	

			APPLICATION FOR ESCC QUALIFICAT	ION APPROVAL	Page 3		
and a	ESCCC Component Title: Integrated Circuits, Silicon, Monolithic, CMOS, Cell-Based Array, based on Type ATMX150RHA – Ph2 Digital Only 22Mgates 5ML+Thick Metal MMT						
	Executive Member: CNES Date: 12/03/2021						
Non compli	ance to ESCC requirements:				13		
No.:	Specification		Paragraph	Non compliance	9		
Additional t	asks required to achieve full com	npliance for ESCC	qualification or rationale for acceptability of	of noncompliance:	14		
Executive N	Manager Disposition				15		
Application Action / Rev Date:	Approval: Yes ⊭ marks:	No 🗆		SH Digitally by Britte Date: 20 10:54:16	/ signed a Schade)21.05.28 5 +02'00'		
				B. Schade: Head of the Produ and Safety Depar	ict Assurance tment		

	AP	Page 4	4				
ESCC	Component Title:	Component Title: Integrated Circuits, Silicon, Monolithic, CMOS, Cell-Based Array, based on Type ATMX150RHA – Ph2 Digital Only 22Mgates 5ML+Thick Metal MMT					
	Executive Member:	CNES	Date: 12/03/2021	372			
ANNEX 1: LIST OF TESTS DONE TO SUF	PPORT QUALIFICATI	ON			16		
Tests conducted in compliance with: ESCO	C 9000						
 ESCC 9000 generic specification Or PID-TFD Tests vehicle identification/description:	on; Chart F4 (for ESCC (for ESCC/QML	C/QPL parts); parts)					
SAMRH71 CQFP-256 SAMRH71 has be Nevertheless, SA Circuit 002OP us NVM block and p needs for micropi the ATMX150RH The qualification flight models scree (http://ww1.micro burn-in (Mil-STD- See DL6.8.3 ESC	een designed in co MRH71 embarks 2 ed for ATMX150RH rogrammable I/O's. rocessors. SAMRH A SEC 002OP (97M has been performe eening is compliant chip.com/download .883 TM1015A). CC Evaluation Repo	mpliance with ATMX150RHA design specific entities not covered by the IA ESCC qualification (ESCC certific These features not mandatory for A 71 also embarks more transistors th A Xtors compared to a maximum co d with flight models randomly chose with -SV requirements as described s/en/Quality_ReliabilityDocs/AEQAC	a rules. ATMX150RHA Standard Eval cate 359 valid until 25 April 20 ASICs are necessary to meet of an the maximum number cover verage of 90M Xtors). n from 3 diffusion/inspection lo in AEQA0242 J242_DS60001546B.pdf), with JRH71, December 2020)	uation 21): a customer ered by ots. The a static			

Detail Specification reference: 9512/006

Subgroup	Test	Tick when done	Conditions	Date Code Diffusion Lot	Tested Qty	No. of Rejects	Comments if not performed. Comments on Rejection
	Mechanical Shock		MIL-STD-883, Test Method 2002B		15	0	5+45 pulses
	Vibration	\boxtimes	MIL-STD-883, Test Method 2007A	A68AN00000	15	0	12+108 sweeps
	Constant Acceleration	\boxtimes	MIL-STD-883, Test Method 2001E	(15 parts)	15	0	Y1
group	Seal Test	\boxtimes	MIL-STD-883, Test Method 1014		15	0	
al Sub	3 Temperature Electrical Test	mperature 3 Temperature 4 trical Test Electrical Test	A68ARA25UH DC2005	15	0		
chanic	External Visual Inspection		MIL-STD-883, Test Method 2007	(15 parts)	15	0	
tal/Me	Thermal Shock	\boxtimes	MIL-STD-883. Test Method 1011C		15	0	15+85 cycles
nmeni	Temperature Cycling	\boxtimes	MIL-STD-883. Test Method 1010C	4694000000	15	0	100 cycles
Envirc	Moisture Resistance	\boxtimes	MIL-STD-883, Test Method 1004	DC2004	15	0	
	Seal Test		MIL-STD-883, Test Method 1014	(15 parts)	15	0	
	3 Temperature Electrical Test		3 Temperature Electrical Test		15	0	
	External Visual Inspection		MIL-STD-883, Test Method 1010		15	0	

Subgroup	Test	Tick when done	Conditions	Date Code Diffusion Lot	Tested Qty	No. of Rejects	Comments if not performed. Comments on Rejection
	Operating Life		MIL-STD-883, Test Method 1005	4000h,			
Endurance Subgroup	Intermediate and End-Point Electrical Measurements		Intermediate and End-Point Electrical Measurements in the Detail Specification	Tamb=125°C, Vccmax A68AQ00000 DC2004 Si-lot DGR3N.1 (15 parts) A68AN00000 DC1952 Si-lot DGR3P.1 (16 parts)	45 45	0	
				A68ARA25UH DC2005 Si-lot DGR3Q.1 (14 parts)	45	0	
	Seal (Fine and Gross Leak)		MIL-STD-883, Test Method 1014				
	External Visual Inspection		ESCC Basic Specification No. 20500				
roup	Permanence of Marking		ESCC Basic Specification No. 24800				
Subg	Terminal Strength		MIL-STD-883, Test Method 2004				Covered by ATMX150RHA ESCC
Capability	Internal Visual Inspection		ESCC Basic Specification No. 20400				qualification tests ESCC certificate 359 valid until April 2021
mbly 0	Bond Strength		MIL-STD-883 Test Method 2011				
Asse	Die Shear or Substrate Attach Strength		MIL-STD-883 Test Method 2019 or 2027				
Additional Tests	Flash memory write/erase endurance cycling		MIL-STD-883 Test Method 1033	A68AQ00000 DC2004 Si-lot DGR3N.1 (15 parts)	15	0	Write/Erase endurance cycling has been performed over the temperature range [0°C, 85°C]. Post- endurance electrical tests have been done over the military temperature range [-55/25/125°C]. Endurance 1 kcycle, 85°C, Vccmax, page mode Electrical test 3-temperature

	Flash memory write/erase endurance cycling	MIL-STD-883 Test Method 1033	A68AN00000 DC1952 Si-lot DGR3P.1 (16 parts)	16	0	Write/Erase endurance cycling has been performed over the temperature range [0°C, 85°C]. Post- endurance electrical tests have been done over the military temperature range [-55/25/125°C]. Endurance 10 kcycle, 25°C, Vccmax, page mode Electrical test 3-temperature
	Flash memory write/erase endurance cycling	MIL-STD-883 Test Method 1033	A68ARA25UH DC2005 Si-lot DGR3Q.1 (14 parts)	14	0	Write/Erase endurance cycling has been performed over the temperature range [0°C, 85°C]. Post- endurance electrical tests have been done over the military temperature range [-55/25/125°C]. Endurance 1 kcycle, 0°C, Vccmax, page mode Electrical test 3- temperature
	Data Retention	JESD22A117	A68AQ00000 DC2004 Si-lot DGR3N.1 (15 parts) A68AN00000 DC1952 Si-lot DGR3P.1 (15 parts) A68ARA25UH DC2005 Si-lot DGR3Q.1 (15 parts)	45	0	Data retention has been performed up to 1000h at 250°C. Electrical tests have been done over the military temperature range [- 55/25/125°C]. 700 hours, 250°C, Elect. test 3- temperature 1000 hours 250°C, Elect. test 3- temperature
	Electrical Latch-Up	JEDEC78	DFNPJA25SV DC1947 Si-lot CQFP-256	6	0	Current injection 100mA, Overvoltage 1.5*Vccmax, Class I: 25°C ambient Class II: 125°C ambient
	ESD (HBM & CDM)	MIL-STD-883 Test Method 3015 ANSI/ESDA/JEDEC JS-002	A68AN00000 DC1952 Si-lot CQFP-256	3 3	3 0	ESD HBM level is class 0 (<250V). The low level shall be improved in the coming revision E of the die 77906. ESD CDM levels is class C0a (<125V) The revision E of the die 77906 will also improve the CDM level.
	Construction Analysis		Die analysis DGR3P.1 Si-lot Assembly analysis A68ARA25UH DC2005	Х	Х	OK

Radiation Tests	TID ESA/SCC 22900 MIL-STD-883 Test Method 1019	DGR3N.1 (9 parts) DGR3P.1 (10 parts) DGR3Q.1 (8 parts)	27 27	0	Tested up to 150 krad(Si) without NVM (22biased & 5unbiased) 15 krad(Si) with NVM (22biased & 5unbiased)
	Heavy lons Single Event Latch- Up Single Event Upset ESA/SCC 25100 EIA/JESD57	DFNPH.1	3	0	SEL: No SEL events have been observed up to a LET of 62.2 MeV.cm²/mg @Vccmax @125°C. SEU: See report

		AF	PLICATION FOR ESCC QUALI	FICATION APPROVAL		Page 7			
ES	SCC	Component Title:	Integrated Circuits, Silicon, Mo on Type ATMX150RHA – Ph2 MMT	nolithic, CMOS, Cell-Bas Digital Only 22Mgates 5M	ed Array, based ⁄IL+Thick Metal	Appl. No.			
		Executive Member:	CNES	Date:	12/03/2021	372			
	NOTES ON THE	COMPLETION OF TH	E APPLICATION FORM FOR E	SCC QUALIFICATION A	PPROVAL				
ENTRIES	shall indicate	the title of the compor	nent as given in its detail specifica	ation or the name of the s	eries or family:	the entering			
1 of in Heading	date; — the seria	al number and the suff	fix of the form.	alon of the name of the 3	ches of family,	and entering			
Box 1	shall provide details given in table; in particular there shall be listed - the variants or range of variants; the range of components by using the ESCC code for values tolerances, etc.; the designation given in detail specification as 'based on';under Test Vehicle enter either a cross or the specific characteristic capable to identify the component tested; — under component similar enter a cross.								
Box 2 and 3	Manufacturer's n	ame and location of p	lant where the components were	manufactured and tested	d.				
Box 4	Generic and deta	ail specifications used	during qualification program.						
Box 5	Reference to tes	t report(s) submitted in	n support of application.						
Box 6	Enter details to id	dentify the PID that wa	as applicable at the time the quali	fication lot was manufact	ured.				
Box 7	If the PID was ev reasons for chan	olved after qualification ges. Major changes s	on lot manufacture, adequate det hall be clearly marked.	ails of such evolution sha	II be provided toge	ether with			
Box 8	The box serves to identify the current PID and the Executive Representative that has verified it together with the date of this occurrence.								
Box 9	This box can be completed only after a physical visit to the plant to confirm that the practices, procedures, materials, etc. used in manufacturing the components are as described in the PID. This survey shall be carried out in accordance with the requirements of ESCC Basic Specification No. 20200 and its findings shall be recorded.								
Box 10	Details entered shall be sufficient to evidence that an evaluation program according to ESCC Basic Specification No. 22600 has been performed and that the results thereof are summarized in the survey and test reports. If the evaluation program has not been carried out according to established ESCC documents, the applicant Executive Representative shall provide alternative data and declare its assessed degree of satisfactory compliance with the ESCC basic requirements. Reference shall be made to the reports on Destructive Physical Analysis (DPA), Failure Analysis and Non conformance (NCCS) issued during the Evaluation and/or Qualification Phase.								
Box 11	Enter the name of	of the Executive Coord	dinator and the signature.						
Box 12	To be used wher in the relevant Bo	n there is a need to ex ox. Box 12 can be bro	pand any of the boxes from 1 thr ken into 12a, 12b, etc. if several l	ough 10. Identify box affe Boxes have to be expand	ected and reference led.	e the Box 12			
Box 13	Fill table as requ	ested.							
Box 14	Fill in any additio	nal tasks required to a	achieve full compliance.						
Box 15	All Executive rec QML entry, letter	ommendations on the s to the manufacturer	application itself, special condition, etc. shall be entered clearly in B	ons or restrictions, modifient or restrictions, modifient or 15, signed by the ES/	cations of the QPL A Representative.	or ESCC			
Box 16	Fill in Table as re	equested.							
Box 17	Confidential deta	ills of PID changes sh	all be provided.						
Box 18	State noncomplia nonconformance	ance with reference to shall be sequentially	specification(s) and paragraph(s numbered. If relevant state 'None). To simplify reference in '	n Box 18 each				
Box 19	Any additional ac accepted by the	ction deemed necessa ESCC Executive shou	ary by the Executive Representati uld be listed herein or the reason(ve to bring the submitted s) to accept the nonconfo	data to a standar ormance.	d likely to be			
Box 20	Additional Comm	nents							